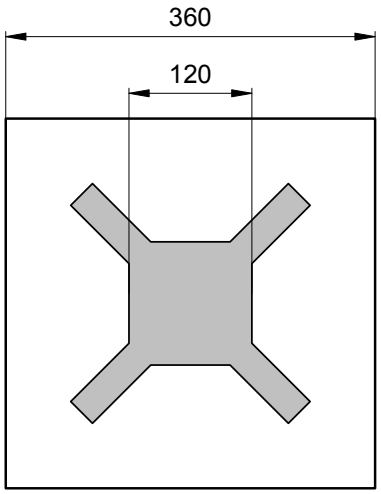
LED - Chip

ELC-870-17-2

Preliminary 10.04.2007 rev. 07/06

Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	P (anode) up



LED-14

typ. dimensions (µm)

typ. thickness
160 (±20) µm

anode
gold alloy, 1.5 µm

cathode
gold alloy, 0.5 µm
dotted, 25% covered

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		1.4	1.6	V
Reverse voltage	I_R = 100 µA	V_R	5			V
Radiant power[1]	I_F = 20 mA	Φ_e	4.0	6.0		mW
Radiant power[2]	I_F = 20 mA	Φ_e		11.0		mW
Peak wavelength	I_F = 20 mA	λ_p	855	870	880	nm
Spectral bandwidth at 50%	I_F = 20 mA	$\Delta\lambda_{0.5}$		45		nm
Switching time	I_F = 20 mA	t_r, t_f		10/20		ns

[1]Measured on bare chip on TO-18 header with *EPIGAP* equipment

[2]Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	Φ_e(typ) [mW]	V_F(typ) [V]	Quantity
ELC-870-17-2				

Packing: Chips on adhesive film with wire-bond side on top

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